

In the Abstract:

## ABSTRACT OF THE DISCLOSURE

### ~~Semiconductor laser device~~

~~The invention relates to a~~ A semiconductor laser device comprising an optically pumped surface-emitting vertical emitter region (2) which has an active radiation-emitting vertical emitter layer (3) and has at least one monolithically integrated pump radiation source (5) for optically pumping the vertical emitter region (2), which has an active radiation-emitting pump layer (6). ~~According to the invention, the~~ The pump layer (6) follows the vertical emitter layer (3) in the vertical direction and a conductive layer (13) is provided between the vertical emitter layer (3) and the pump layer (6). Furthermore, a contact (9) is applied on the side of the semiconductor laser device which is closer to the pump layer (6) than to the conductive layer (13). An electrical field can be applied between this contact (9) and the conductive layer (13) for generating pump radiation (7) by charge carrier injection.

~~Significant Figure: Figure 1~~